

Fig. 1A

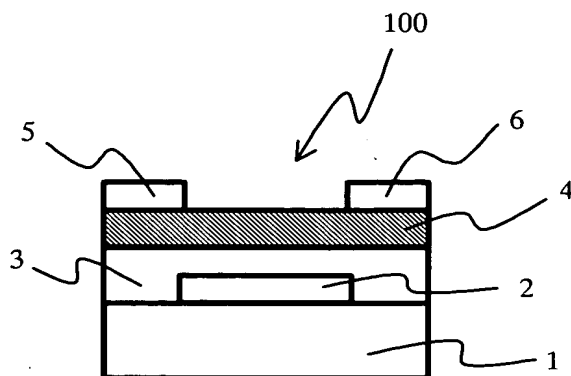


Fig. 1B

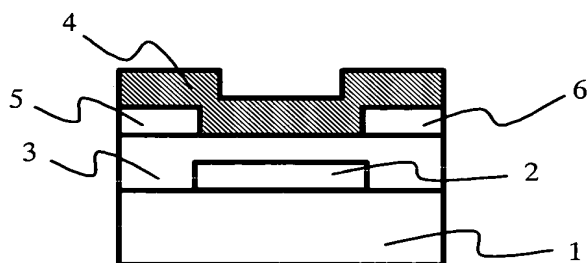


Fig. 1C

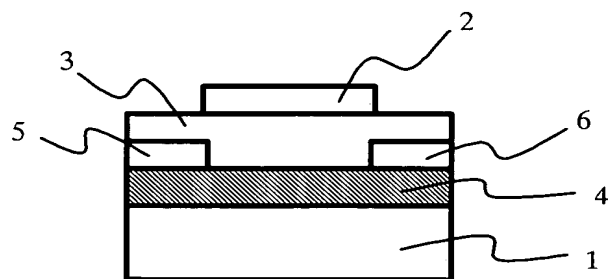


Fig. 1D

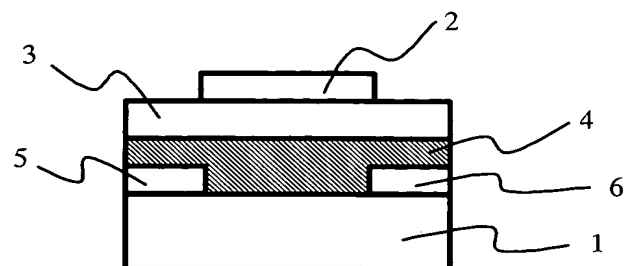


Fig. 2A

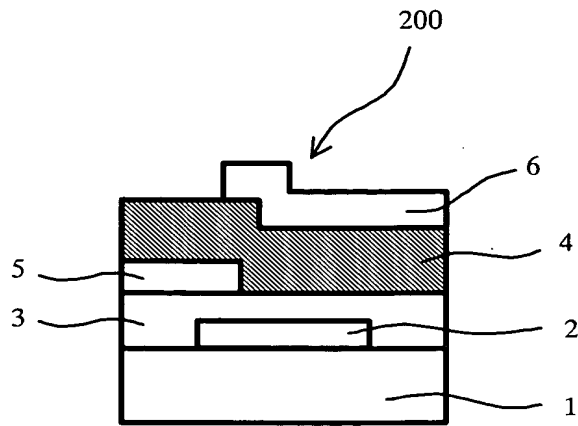
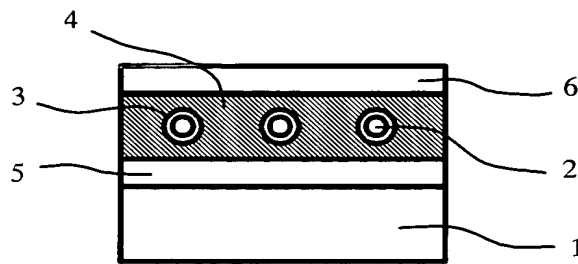


Fig. 2B



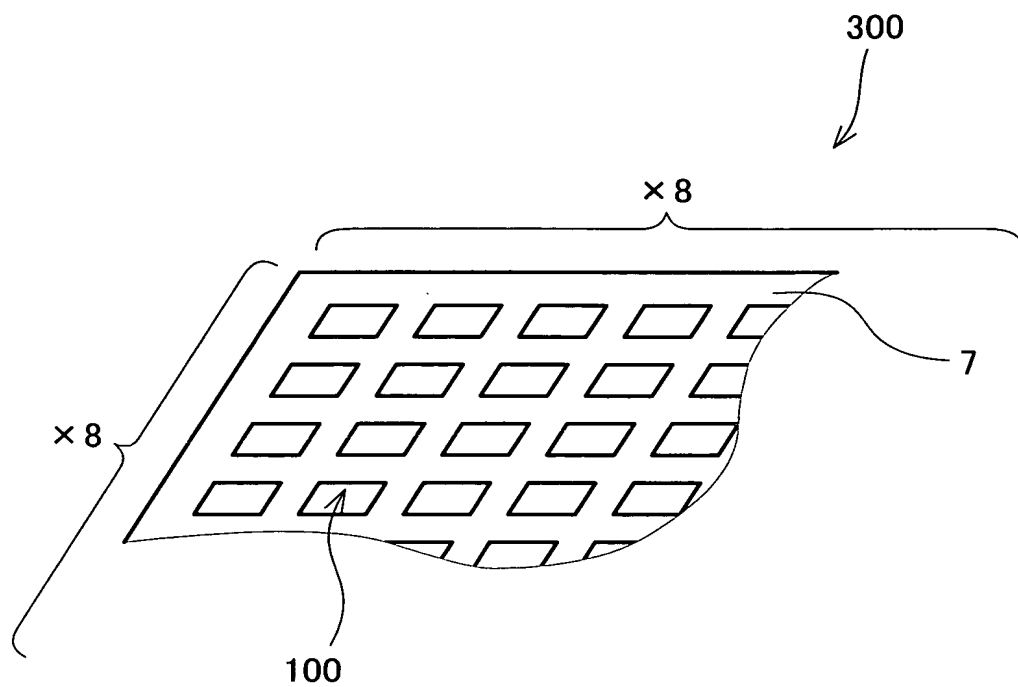


Fig. 3

Fig. 4A

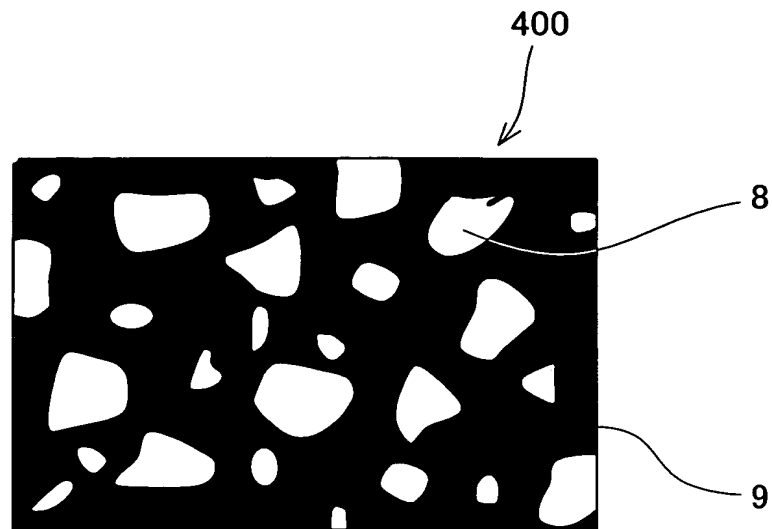
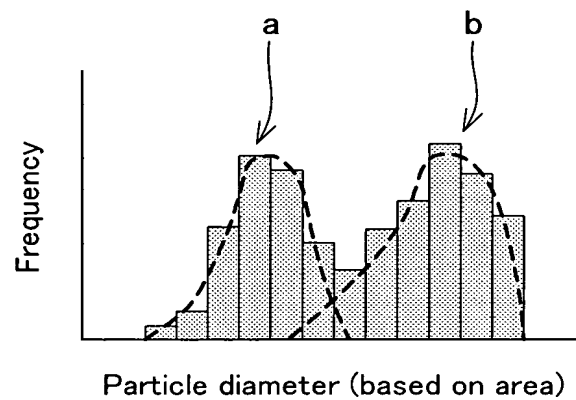


Fig. 4B



P-type silicon crystal 1 Average particle diameter 20 $\mu$ m (volume%)	P-type silicon crystal 2 Average particle diameter 1.5 $\mu$ m (volume%)	Total filling rate (volume%)
0	0	0
10	0	10
20	0	20
40	0	40
40	15	55
40	20	60
40	25	65

Fig. 5

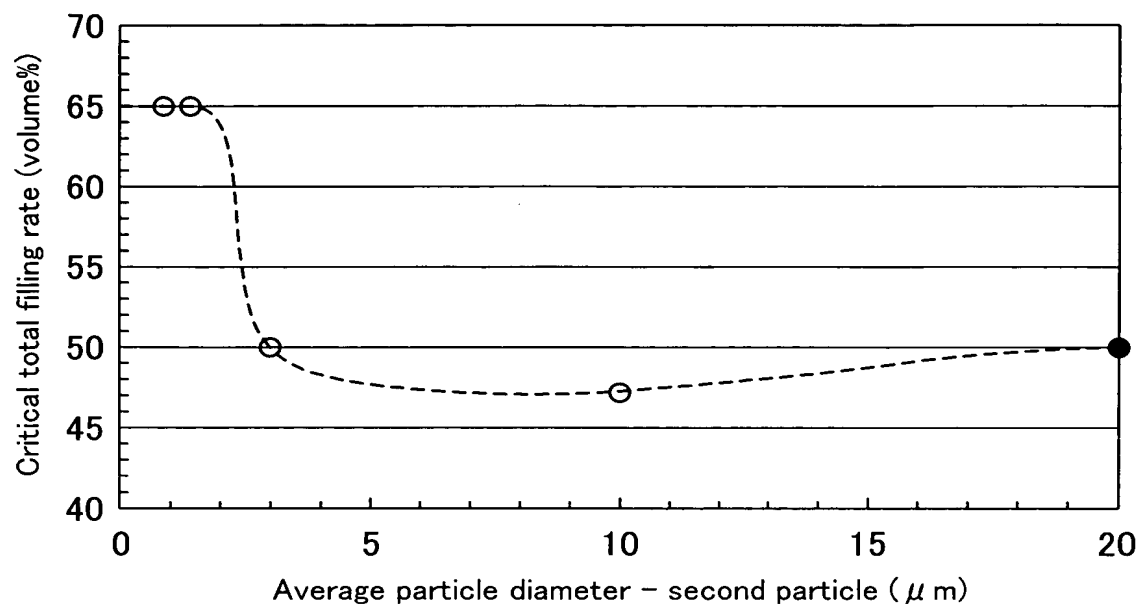
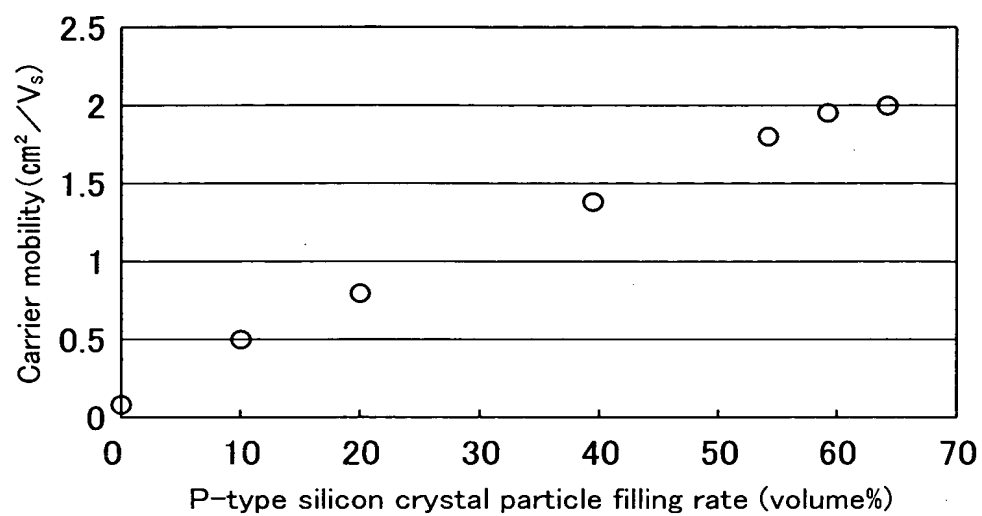


Fig. 6

**Fig. 7**

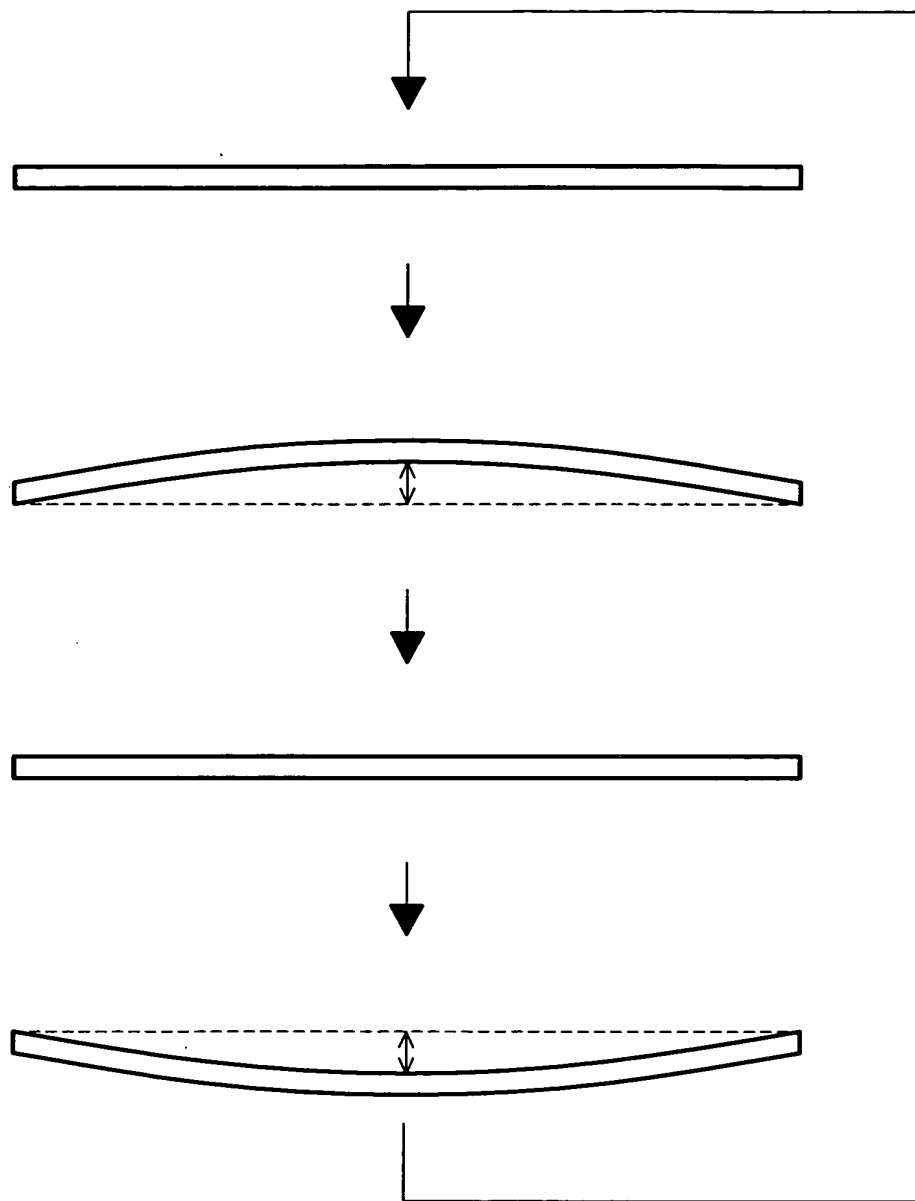


Fig. 8



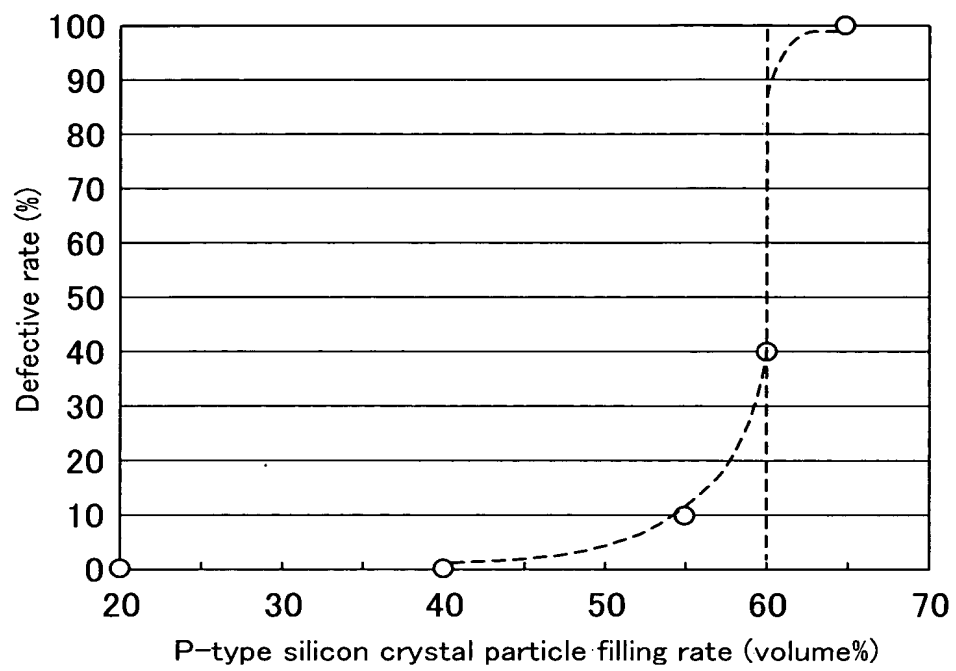


Fig. 9

Cu particle 1 Average particle diameter 10 $\mu$ m (volume%)	Cu particle 2 Average particle diameter 1 $\mu$ m (volume%)	Total filling rate (volume%)
0	0	0
10	0	10
30	0	30
40	5	45
40	20	60

Fig. 10

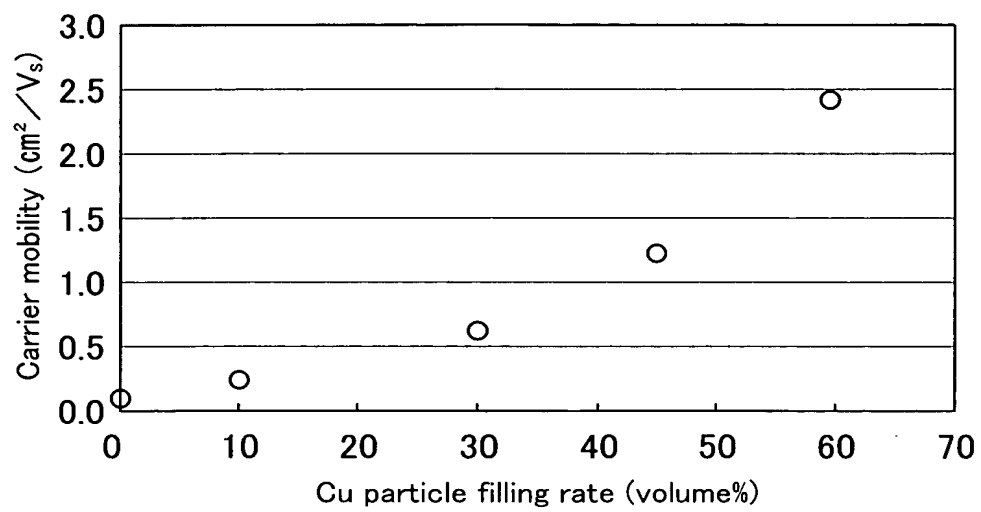


Fig. 11

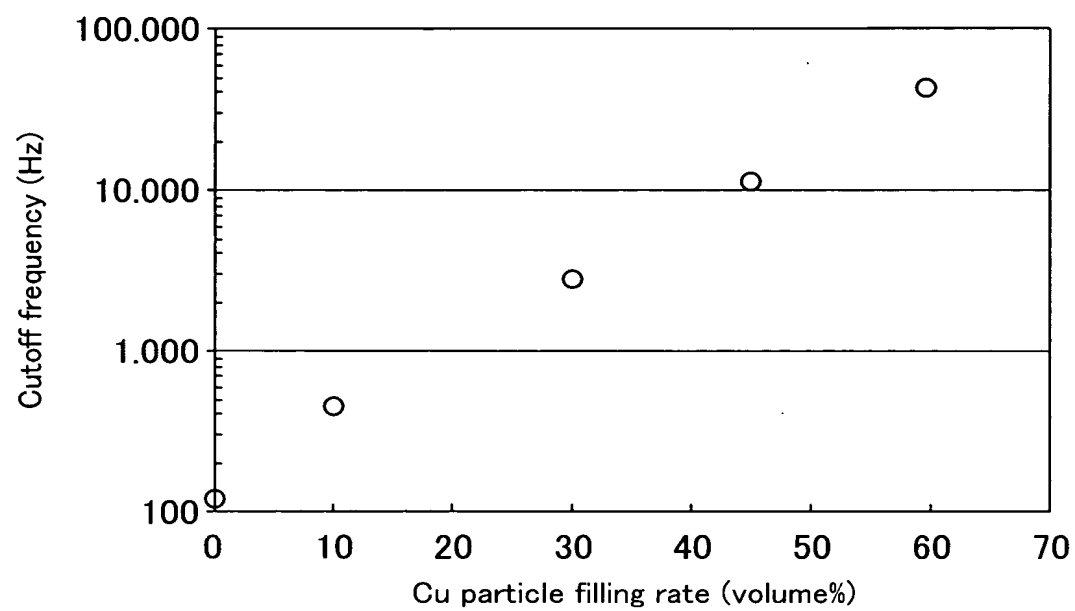


Fig. 12

	P-type silicon crystal 1 Average particle diameter 20 $\mu$ m (volume%)	Cu particle 2 Average particle diameter 1 $\mu$ m (volume%)	Total filling rate (volume%)	Carrier mobility (cm <sup>2</sup> /V <sub>s</sub> )	Cutoff frequency (kHz)
1st embodiment	40	0	40	1.4	2.2
3rd embodiment(1)	40	5	45	1.9	4.7
3rd embodiment(2)	40	10	50	2.5	8.5

Fig. 13

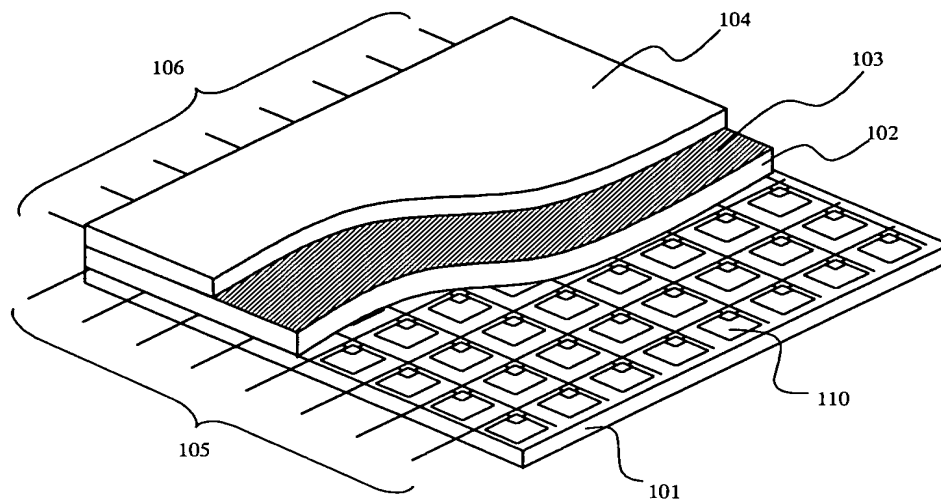


Fig. 14

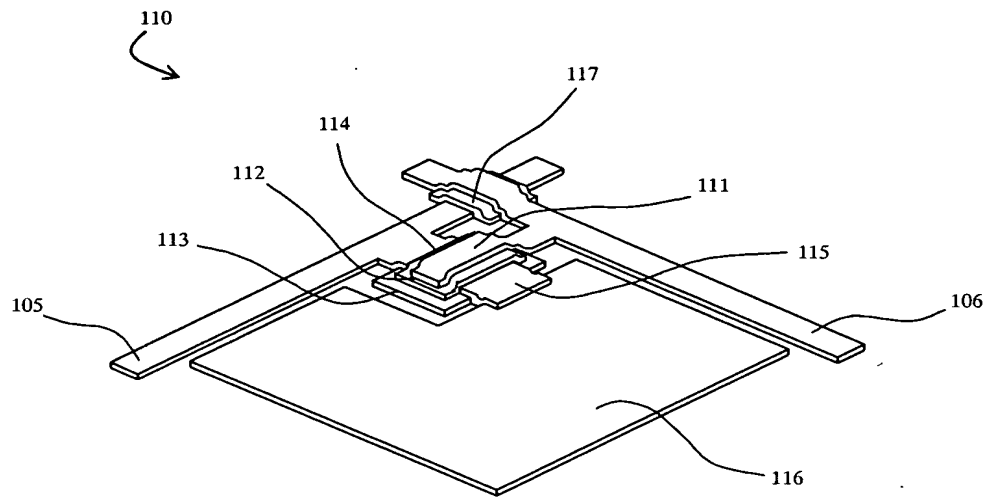


Fig. 15

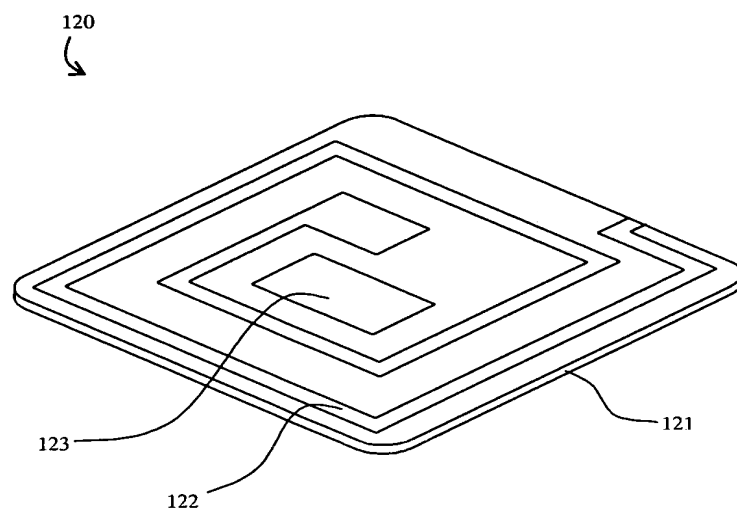


Fig. 16



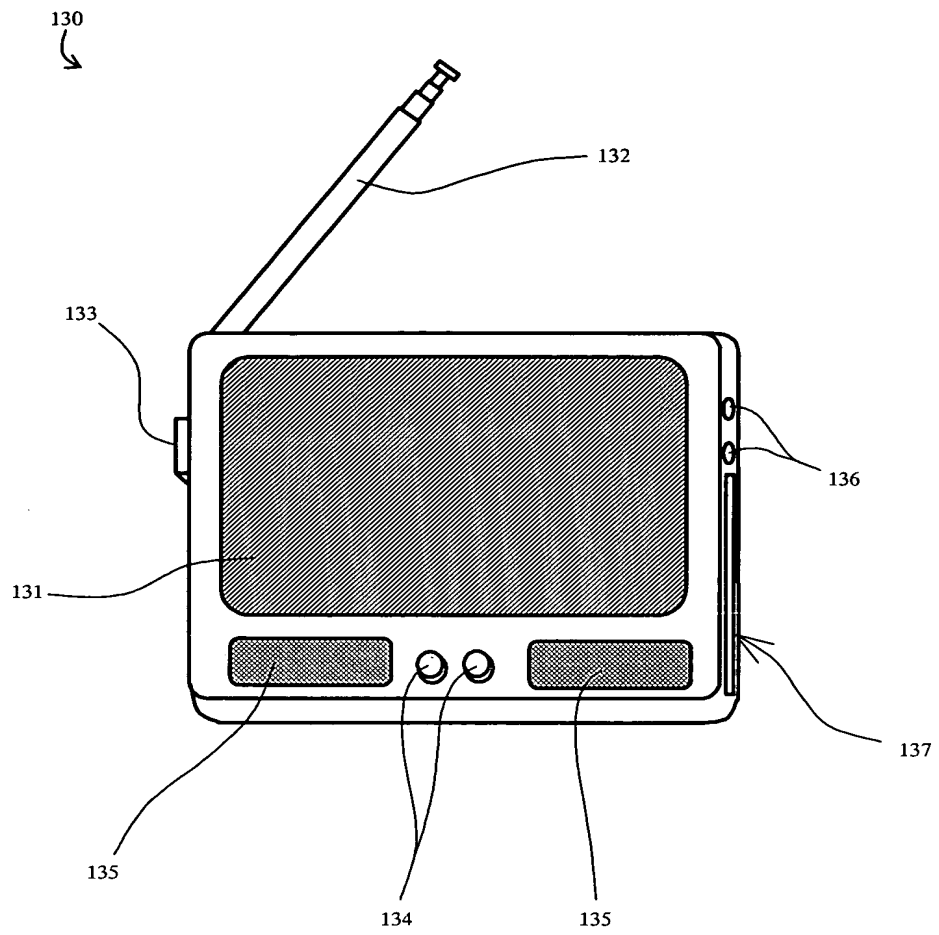


Fig. 17

140  
↘

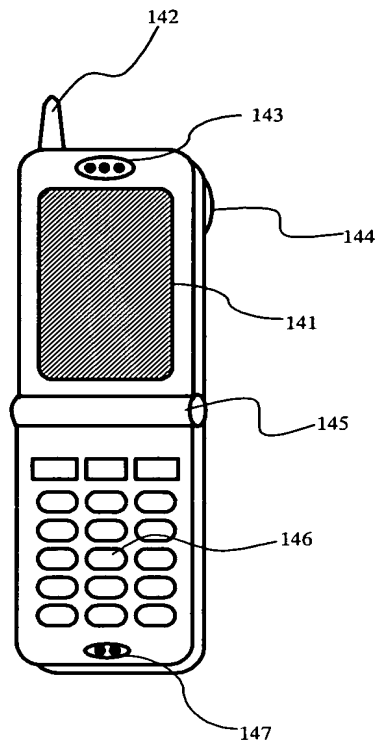


Fig. 18

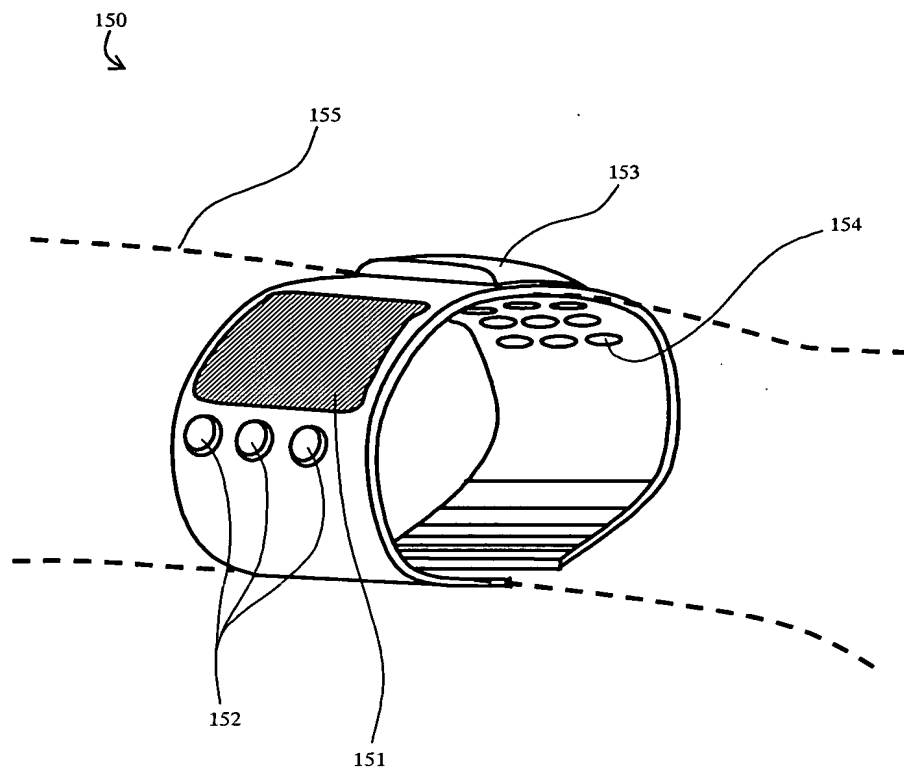


Fig. 19

REFERENCE MARK (1)

- 1 Substrate
- 2 Gate electrode
- 3 Gate insulating layer
- 4 Semiconductor layer
- 5 Source electrode
- 6 Drain electrode
- 7 Plastic substrate
- 8 Particle
- 9 Organic semiconductive material
- 100 TFT
- 101 Plastic substrate
- 102 Organic EL layer
- 103 Transparent electrode
- 104 Protective film
- 105 Source electrode line
- 106 Gate electrode line
- 110 TFT drive circuit
- 111 Gate electrode
- 112 Gate insulating layer
- 113 Semiconductor layer
- 114 Source electrode
- 115 Drain electrode
- 116 Pixel electrode
- 117 Insulating layer
- 120 Radio ID tag
- 121 Plastic substrate
- 122 Antenna portion
- 123 Memory IC portion
- 130 Portable TV
- 131 Display portion
- 132 Receiving portion
- 133 Power switch
- 134 Operation switch
- 135 Sound output device

REFERENCE MARK (2)

- 136 Input/output terminal
- 137 Recording media insertion portion
- 140 Cellular phone
- 141 Display portion
- 142 Receiving/sending portion
- 143 Sound output portion
- 144 Camera portion
- 145 Movable folding portion
- 146 Operation switch
- 147 Sound input portion
- 150 Portable medical device
- 151 Display portion
- 152 Operation switch
- 153 Medical treatment portion
- 154 Transdermal contact portion
- 155 Arm
- 200 TFT
- 300 Semiconductor property evaluation sample
- 400 Sectional surface